GP2W1302YP

IrDA Compliant Transceiver Module
9.6 kb/s to 1.152 Mb/s (MIR)
Low Profile
Low Consumption Current

■Description

The **GP2W1302YP** is an infrared transceiver module for IrDA ver. 1.4 (MIR).
The transceiver consisits of a pin-photo diode, infrared emitter and control IC in a single package.

■Features

1. Compliant with the IrDA 1.4 (MIR)
   Transmission speed : 9.6 kb/s to 1.152 Mb/s
   Transmission distance : 1 m
2. Small package
   L 7.9 × W 2.85 × H 2.15 mm
3. Peak emission wavelength : 870 nm
4. Side view type
5. Soldering reflow type
6. Shield type
7. Low consumption current due to shutdown function
   (Consumption current at shutdown mode : Max. 1.0 μA)
8. Operates from 2.4 to 3.6 V
9. With V_{IO} terminal
10. Compatible with 2.15mm height for cellular phone

■Agency approvals/Compliance

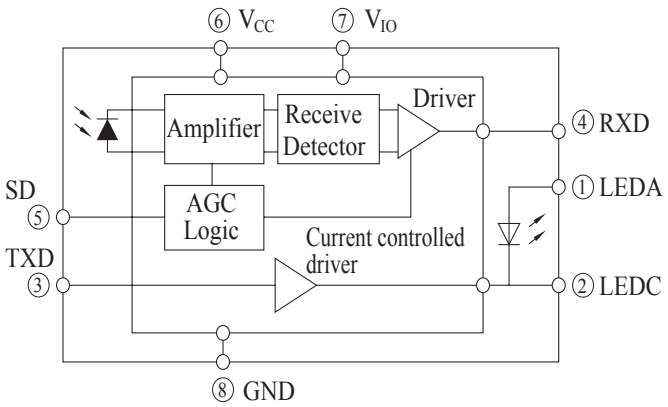
1. Compliant with IEC60825-1 class 1 eye safety standard
2. Compliant with RoHS directive (2002/95/EC)
3. Content status of six substances specified in
   " Management Methods for Control of Pollution Caused by Electronic Information Products Regulation "
   (popular name : *China RoHS*)
   (Chinese : 电子信息产品污染控制管理办法)
   ; refer to page 13
4. Lead (Pb) free device

■Applications

1. Mobile equipment
   (Cellular phone, Pager, Smart phone, PDAs, Portable printer, etc.)
2. Digital imaging equipment
   (Digital camera, Photo imaging printer)
3. POS equipment
4. Personal computers
5. Personal information tools

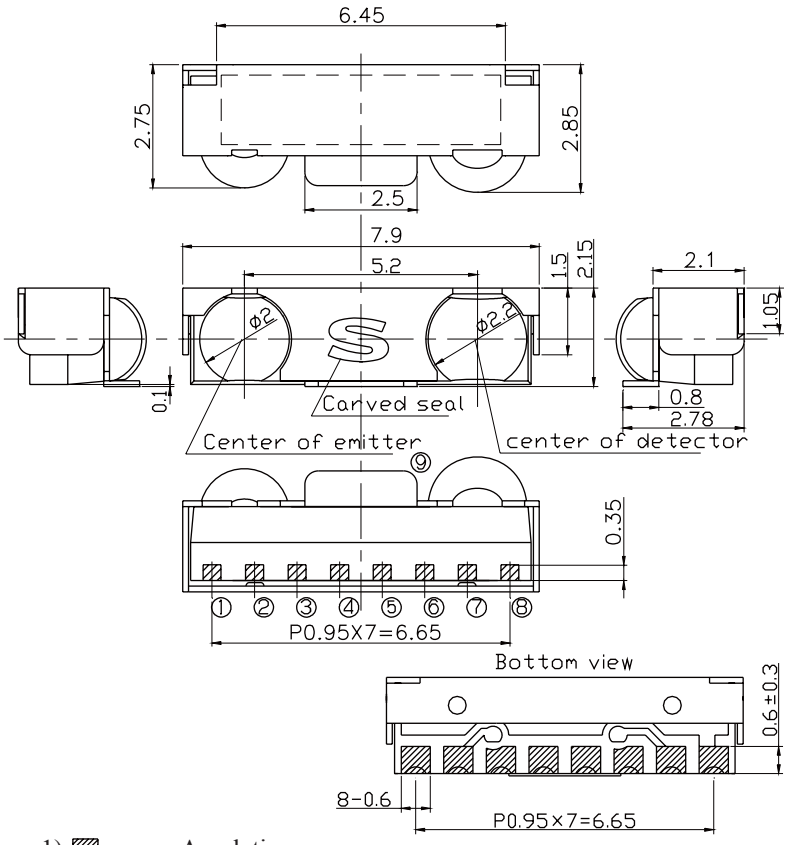
Sheet No.: E3-A00302EN
Date Apr.02.2007

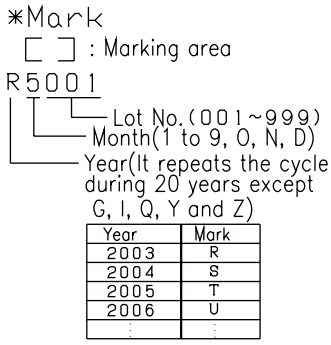
■Block diagram



■Outline Dimensions

(Unit : mm)





Year	Mark
2003	R
2004	S
2005	T
2006	U
⋮	⋮

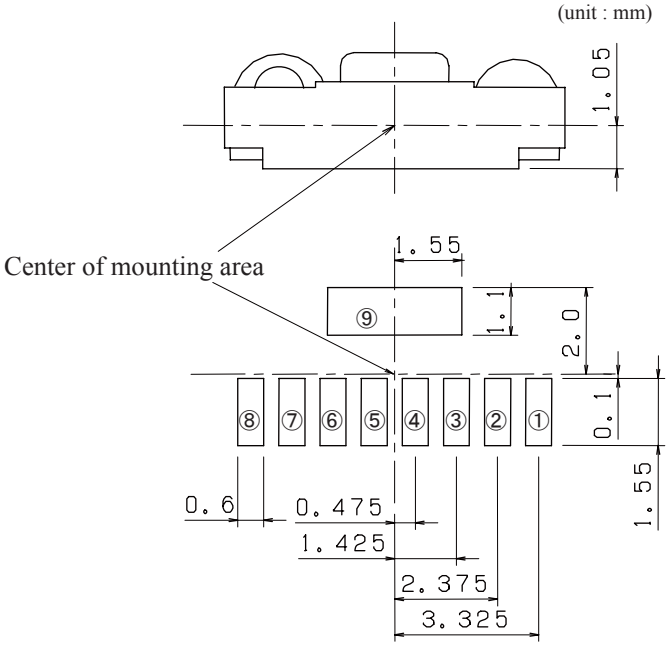
	Terminal	Symbol
①	LED Anode	LEDA
②	LED Cathode	LEDC
③	Transmitter Data Input	TXD
④	Receiver Data Output	RXD
⑤	Shutdown	SD
⑥	V_{CC}	V_{CC}
⑦	Logic I/O levels	V_{IO}
⑧	Ground	GND
⑨	Shield Ground	SGND

1) ▨ area : Au plating
2) Unspecified tolerance shall be ± 0.2 mm
3) Adhesion of resin to the terminal area shall be allowed Max. 0.2 mm

Product mass : approx. 0.08g

■Recommended PCB Foot Pattern

(unit : mm)



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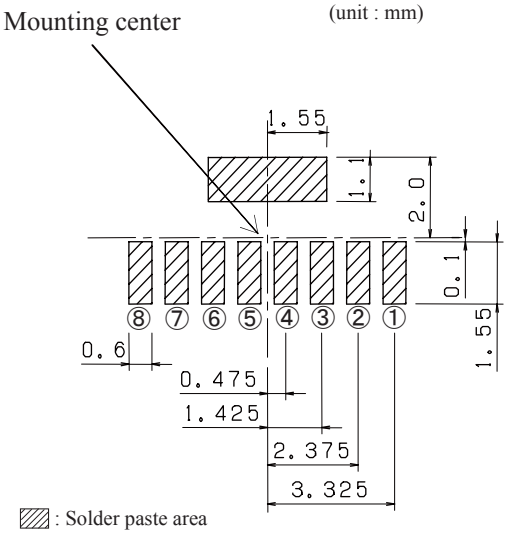
⑨	Shield Ground	SGND

Dimensions in parenthesis are shown for reference.

■Recommended Size of Solder Creamed Paste (Reference)

Dimensions are shown for reference.
Please open the solder mask as below so that the size of solder creamed paste for this device before reflow soldering must be as large as one of the foot pattern land indicated for reference.

(unit : mm)



■Absolute Maximum Ratings

(T_a=25℃)

	Parameter	Symbol	Rating	Unit
	Supply voltage	V_{CC}	-0.5 to 6.0	V
	LED Supply voltage	V_{LED}	-0.5 to 7.0	V
	Transmitter Data Input	TXD	-0.5 to V_{CC}+0.5	V
	Shutdown	SD	-0.5 to V_{CC}+0.5	mA
	Logic I/O levels	V_{IO}	-0.5 to V_{CC}+0.5	mA
*1	Peak forward current	I_{FM}	600	mA
	Operating temperature	T_{opr}	-25 to +85	℃
	Storage temperature	T_{stg}	-40 to +100	℃
*2	Soldering temperature	T_{sol}	260	℃

*1 Pulse operation
*2 Soldering reflow time:10s

■Electro-optical Characteristics

(T_a=25 to +85°C, V_{CC}=2.4 to 3.6V Unless otherwise specified)

	Parameter	Symbol	Rating	MIN.	TYP.	MAX.	Unit
Receiver side	Current consumption at no input signal	I_{CC}	No input signal, output terminal open, V_{ILSD}=0V	—	445	585	μA
	Current consumption at receiving	I_{CC-R}	Output terminal open, V_{ILSD}=0V	—	650	—	mA
	Current consumption at shutdown mode	I_{CC-S}	No input signal, output terminal open, V_{IHSD}=V_{CC}-1.2V	—	0.01	1.0	μA
	High level output voltage	V_{OH}	V_{IO}=1.8V, I_{OH}=0.3mA *3	V_{IO}-0.5	—	V_{CC}	V
	Low level output voltage	V_{OL}	I_{OL}=1mA *3	—	—	0.6	V
	Rise time	t_r	BR=1.152Mb/s, CL=15pF, Ta=25℃ *3	—	—	50	ns
	Fall time	t_f	BR=1.152Mb/s, CL=15pF, Ta=25℃ *3	—	—	40	ns
	Low level pulse width	t_{w1}	t_{W1},Ee1;BR=115.2kb/s, (40mW/sr) ϕ ≦15° t_{W2},E_{e2};BR=1.152Mb/s, (100mW/sr) ϕ ≦15° T_a=25℃ Except for 1st pulse	1.0	—	4.0	μs
		t_{w2}		110	—	500	ns
	Maximum reception distance	L		70	—	—	cm
	Input irradiance	E_{e1}		—	—	8.2	μW/cm^2
		E_{e2}		—	—	20.4	μW/cm^2
	Overload irradiance	E_{e3}		500	—	—	mW/cm^2
	Receiver Latency	t_l		—	—	200	μs
	Receiver wake up time	t_{sdw}	No input signal	—	—	100	μs
	SD input current	V_{isd}	V_{IHSD}=V_{CC}, V_{ILSD}=GND	-0.1	0	+0.1	μA
	SD terminal Input voltage Logic High	V_{IHSD}	Shutdown mode	1.6	—	V_{CC}	V
	SD terminal Input voltage Logic Low	V_{ILSD}	Normal mode	—	—	0.5	V
	Jitter	t_j	BR=1.152Mb/s, Ta=25℃	—	100	150	ns
Transmitter side	Radiant intensity	I_E	ϕ ≦15°, V_{LED}=5V±5%, R_{LED}=4.7Ω, T_a=25℃ *4	50	—	—	mW/sr
	LED peak current	I_{LED}	V_{CC}=3.3V, R_{LED}=4.7Ω, T_a=25℃ *4	—	450	—	mA
	Rise time	t_r	BR=1.152Mb/s, T_a=25℃, V_{LED}=3V *4	—	—	40	ns
	Fall time	t_f		—	—	40	ns
	Peak emission wavelength	λ_p	T_a=25℃	850	870	900	nm
	TXD high level input voltage	V_{IHTXD}	LED(ON),V_{IO}=1.8V	1.6	—	V_{IO}	V
			LED(ON),V_{CC}=V_{IO}=3.3V±0.3V	2.5	—	V_{IO}	V
	TXD low level input voltage	V_{ILTXD}	LED(OFF)	—	—	0.6	V
	TXD high level input current	I_{IHTXD}	T_a=25℃, V_{IHTXD}=1.6V	—	—	50	μA
	TXD low level input current	I_{ILTXD}	T_a=25℃, V_{ILTXD}=0 to 0.6V	—	—	8	μA
	Maximum optical pulse width	T_{OPWM}	TXD pin stuck high	30	—	300	μs

*3 Refer to Fig. 2, 3
*4 Refer to Fig. 4,5,6

■Recommended Operating Conditions

(T_a=25℃)

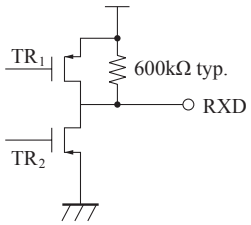
Parameter	Symbol	Rating	Unit
Supply voltage	V_{CC}	2.4 to 3.6	V
LED Supply voltage	V_{LED}	2.4 to 5.5	V
Operating temperature	T_{opr}	-25 to +85	℃
Data rate	BR	9.6k to 1.152M	b/s
Logic I/O levels	V_{IO}	1.5 to V_{CC}	V

■Truth Table

SD	SW	TXD	LED	Receiver	TR1	TR2	RXD
H	Off	L	Off	Don't Care	Off	Off	pull-up
L	On	H	On	Don't Care	Off	On	L(echo)
L	On	L	Off	IrDA Signal	Off	On	L
L	On	L	Off	No Signal	On	Off	H

H:High
L:Low

*RXD equivalent circuit



*TXD equivalent circuit

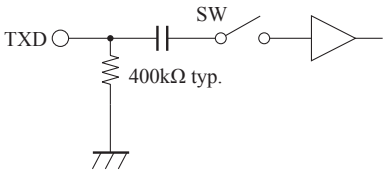
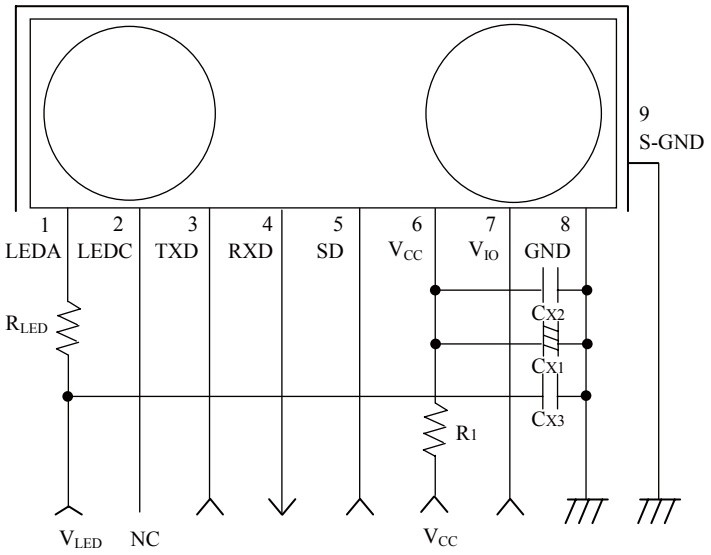


Fig.1 Recommended External Circuit



Components	Recommended values
C_{X1}	10µF/16V(Note1)
C_{X2}	0.47µF(Ceramic)(Note1)
C_{X3}	10µF(Ceramic)(Not1)
R_1(0.125W)	4.7Ω
R_{LED} (0.5W)	4.7Ω(V_{LED}=2.4 to 5.5V) (Note2)

(Note 1) Components choose the most suitable C_{X1}, C_{X2}, C_{X3} according to the noise level and noise frequency of power supply.
(Note 2) In order to guarantee 50mW/sr, V_{LED} is required 4.5 to 5.5V.

Fig.2 Output Waveform Specification (Detector side)

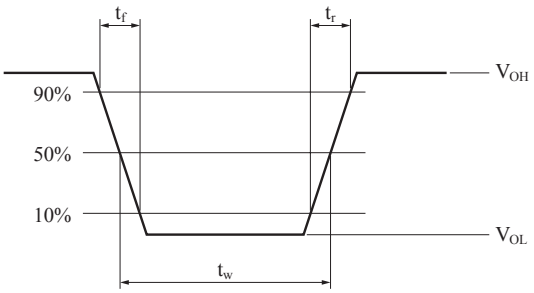
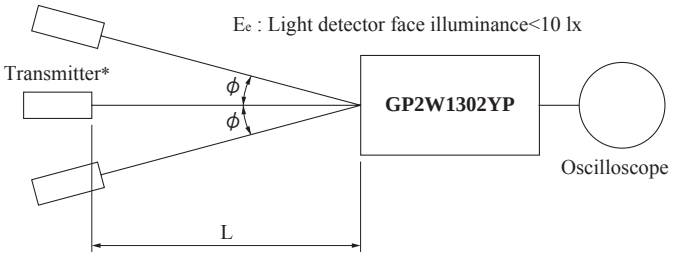
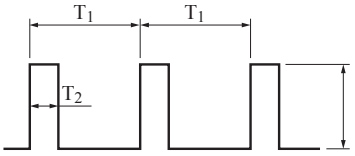


Fig.3 Standard Optical System (Detector side)



ϕ : Indicates horizontal and vertical directions.

Input signal waveform (Detector side)



Radiantion intensity of transmitter
40mW/sr(at BR=115.2kb/s)
100mW/sr (at BR=1.152Mb/s)

At BR=115.2kb/s : T_1=8.68µs, T_2=1.41 to 2.23µs
At BR=1.152Mb/s:T_1=868ns, T_2=217ns

* Transmitter shall use GP2W1302YP (λp=870nm TYP.) which is adjusted the radiation intensity at 40mW/sr (at 115.2kb/s), 100mW/sr (at 1.152Mb/s)

Fig.4 Output Waveform Specification (Transmitter side)

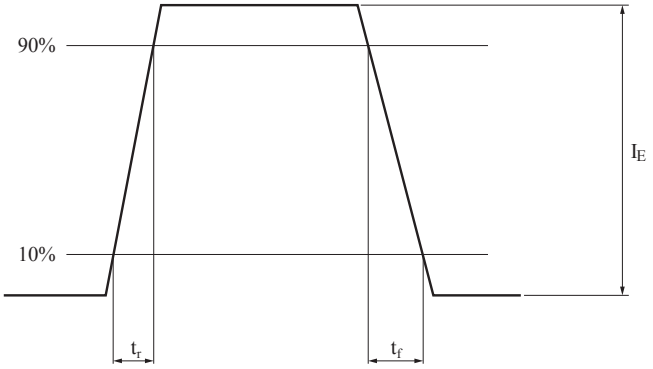


Fig.5 Standard Optical System (Transmitter side)

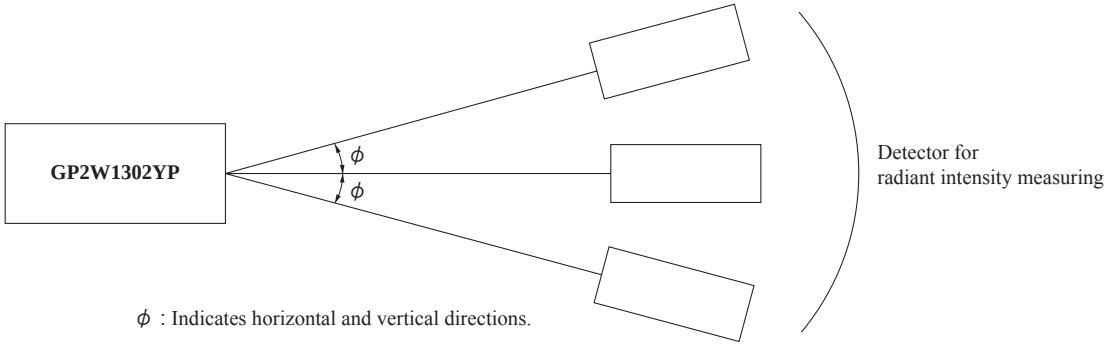


Fig.6 Recommended Circuit of Transmitter side

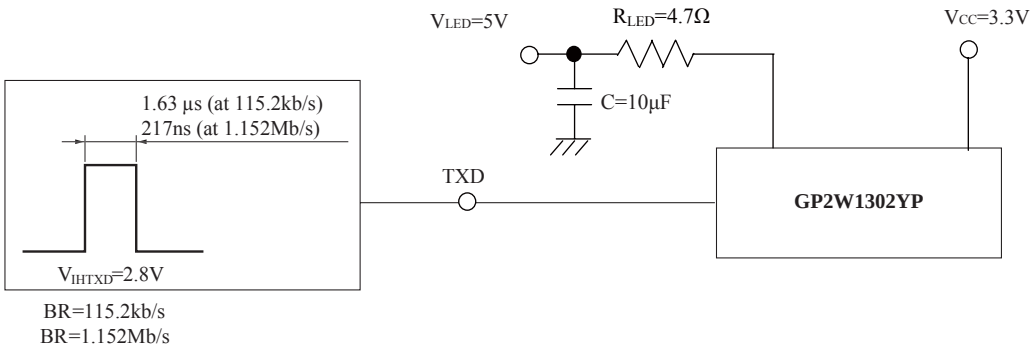
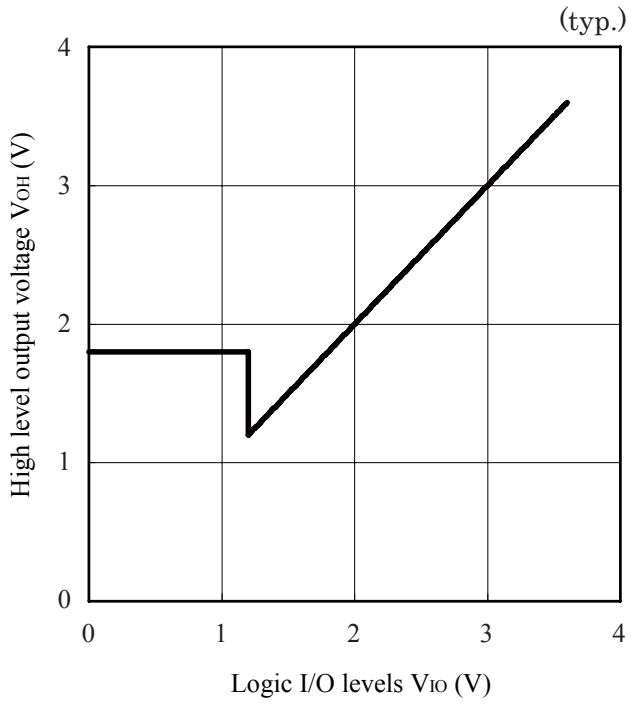


Fig.7 High level output voltage(V_{OH}) vs Logic I/O levels(V_{IO})



■Notes

(1) When the system (program) is designed, the Turn Around Time shall be secured by considering 200 µs or more that is specified to IrDA.
Then, this Turn Around Time means the time when this device does not temporarily detect the signal light, since the transmitted light form the transceiver reaches the detector side of the transceiver.

(2) As it is necessary 100 µs or more (at Ta =25 °C, no input signal) to return from shut-down mode to ready-operation mode, please consider this point at the system (program) designing.
Also, please confirm thoroughly the operation in actual application.

(3) When there is much external disturbing light source is located near this transceiver and the detector face resceiver much external disturbing light, there is case that the pulse other than signal output is generated as noise on output terminal of this transceiver. Please consider the lay-out and structure to reduce disturbing light on the detector face.

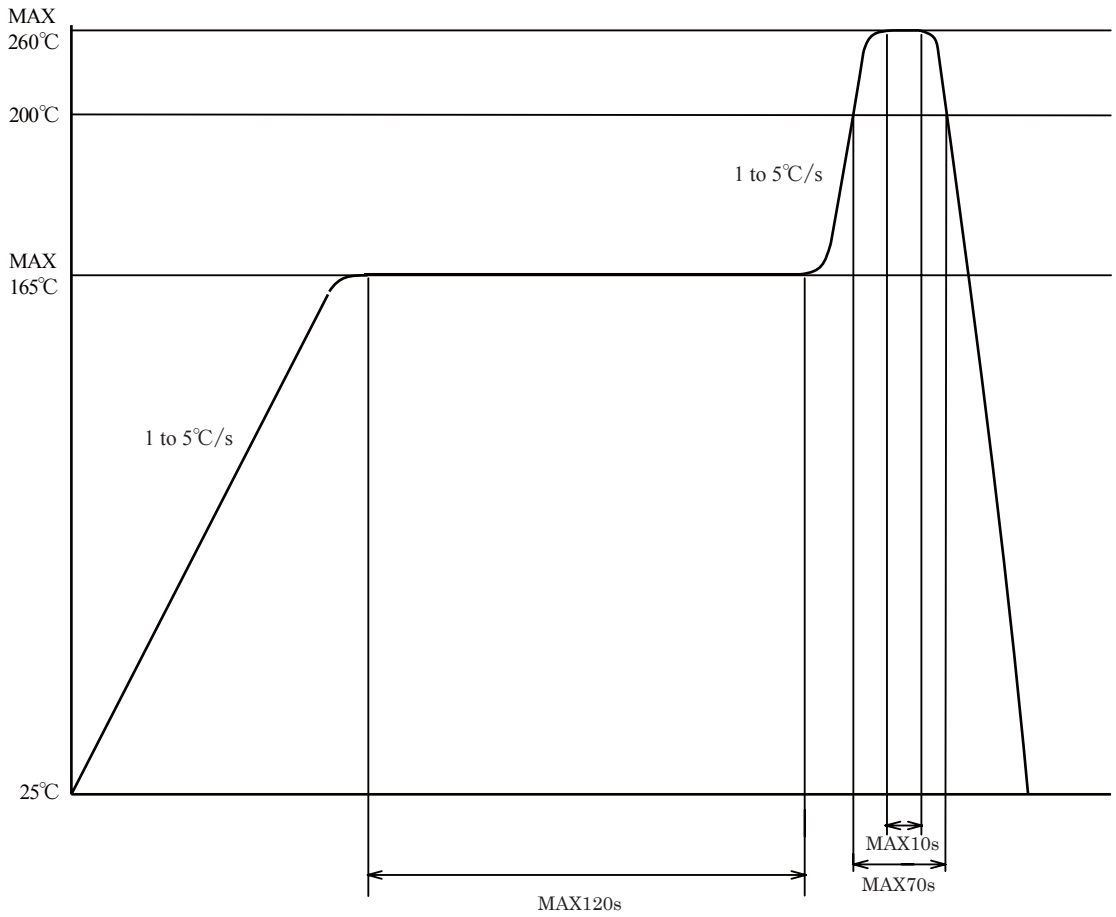
(4) In case that this sensor is adopted in IR communication system, please use it according to the signal method which is specified by [Serial Infrared Physical Layer Link Specification Version 1.4] published by Infrared Data Association. False operation may happen if the different signal method is used.

(5) In circuit designing, make allowance for the degradation of light emitting diode output that results from long continuous operation. (50 % degradation/5 years)

■Soldering Method

1. In case of solder reflow

Please carry out only two times soldering at the temperature and the time within the temperature profile as shown in the figure below. Reflow interval shall be within 3 days under conditions, 10 to 30℃, 70%RH or less.



2. Other precautions

An infrared lamp used to heat up for soldering may cause a localized temperature rise in the resin.
So keep the package temperature within that specified in Item 1. Also avoid immersing the resin part in the solder.
Even if within the temperature profile above, there is the possibility that the gold wire in package is broken in case that the deformation of PCB gives the affection to lead pins. Please use after confirming the conditions fully by actual solder reflow machine.

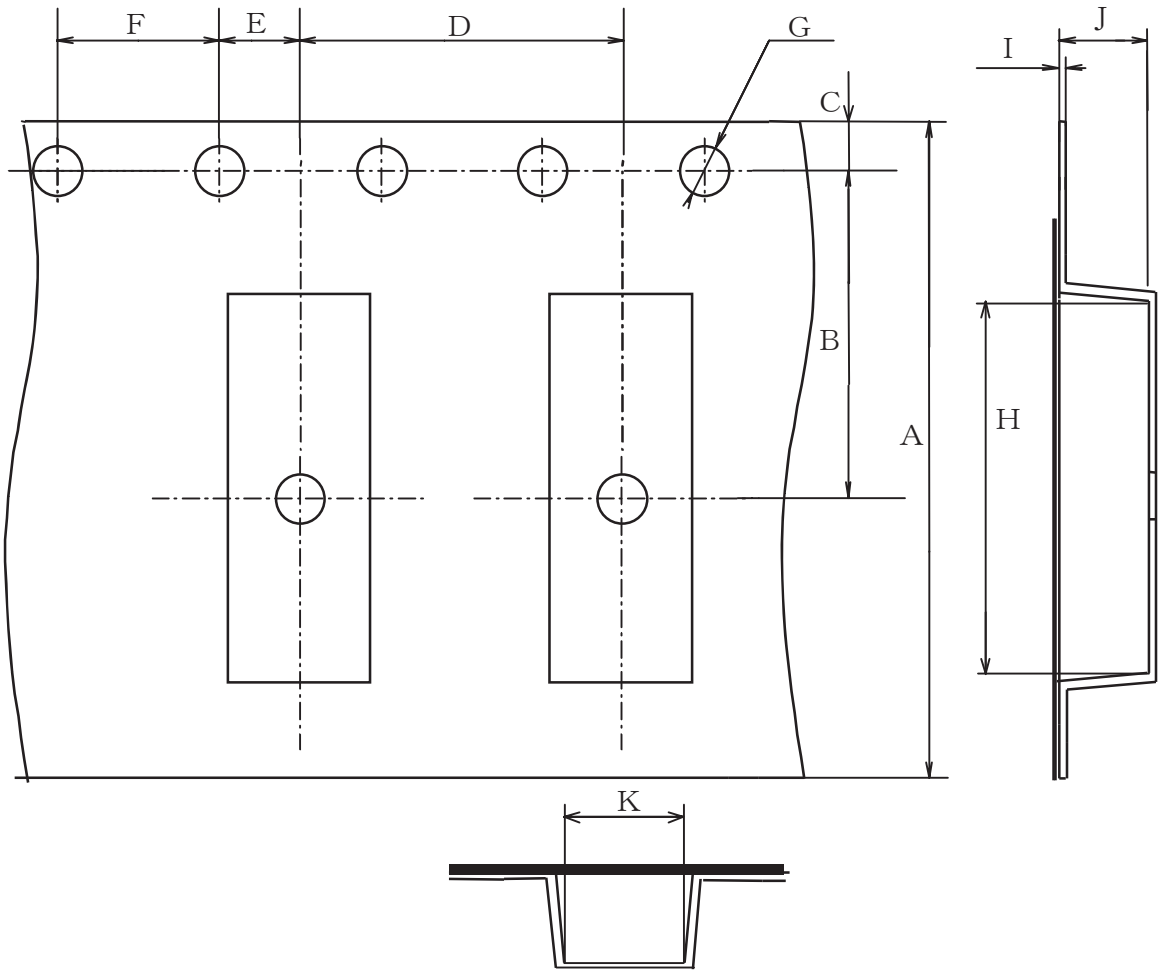
3. Hand soldering

- Soldering iron shall be less than 25W, and temperature of point of soldering iron shall use at 300℃or less.
- Soldering time shall be within 5s.
- Soldered product shall treat at normal temperature.

■Package specification

●Tape and Reel package
2000pcs/reel

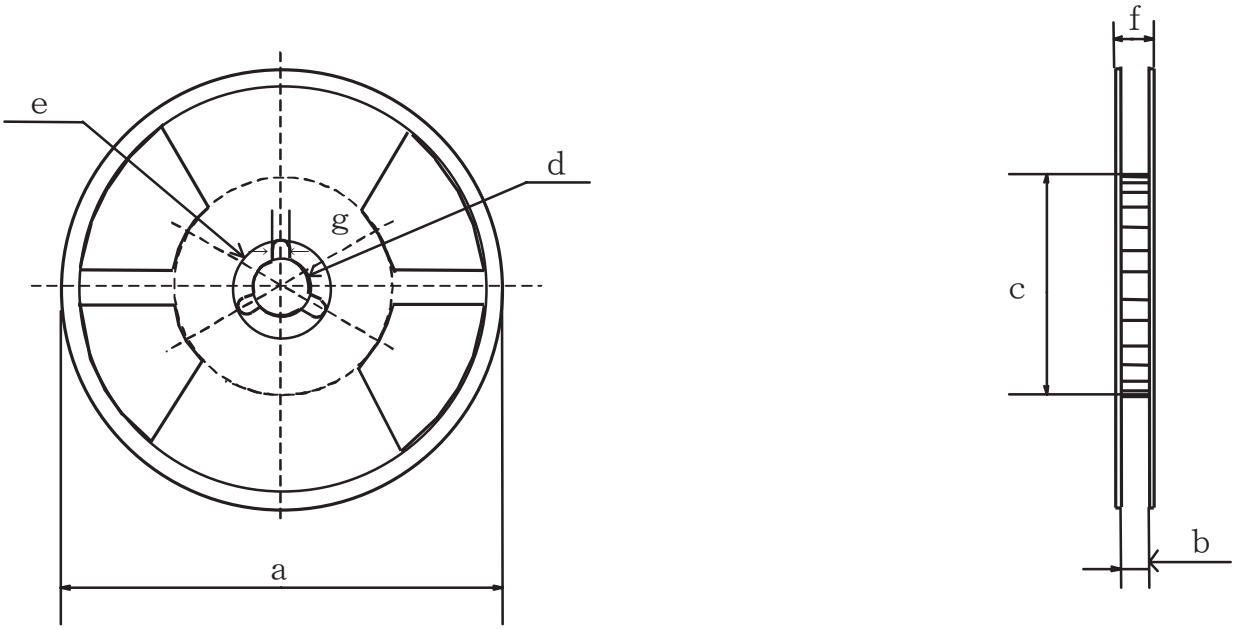
Carrier tape structure and Dimensions



Dimension List (Unit : mm)

A	B	C	D	E	F
16.0±0.3	7.5±0.1	1.75±0.1	8.0±0.1	2.0±0.1	4.0±0.1
G	H	I	J	K	
$\phi\ 1.5^{+0.1}_{-0.0}$	8.25±0.1	0.32±0.05	2.5±0.1	3.15±0.1	

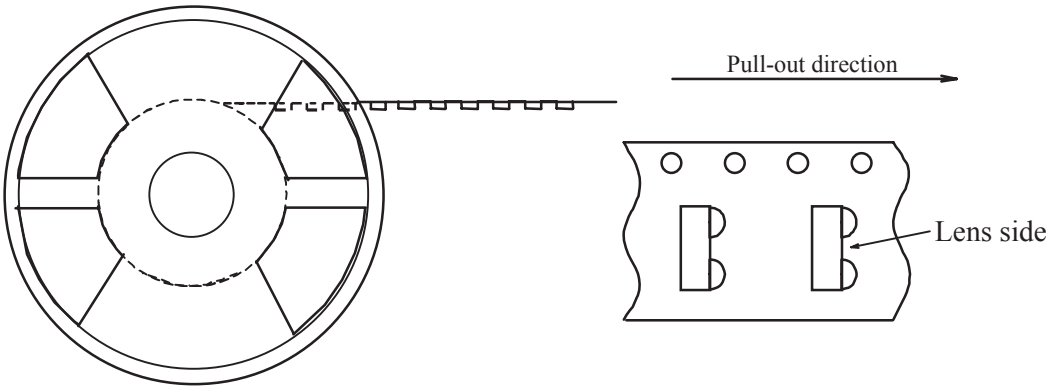
Reel structure and Dimensions



Dimension List (Unit : mm)

a	b	c	d
330±2	17.5±2	100±1	13±0.3
e	f	g	
21±0.8	22.5±2	2±0.5	

Direction of product insertion



●Cleaning Instructions

Solvent cleaning :

Solvent temperature 45℃ or less, Immersion for 3 min or less

Ultrasonic cleaning :

The effect to device by ultrasonic cleaning differs by cleaning bath size, ultrasonic power output, cleaning time, PCB size or device mounting condition etc.
Please test it in actual using condition and confirm that doesn't occur any defect before starting the ultrasonic cleaning. The cleaning shall be carried out with solvent below.

Recommended Solvent materials :

Ethyl alcohol, Methyl alcohol, Isopropyl alcohol

●Presence of ODC etc.

This product shall not contain the following materials.
And they are not used in the production process for this product.
Regulation substances : CFCs, Halon, Carbon tetrachloride, 1.1.1-Trichloroethane (Methylchloroform)

Specific brominated flame retardants such as the PBB and PBDE are not used in this product at all.

• The RoHS directive (2002/95/EC)
This product complies with the RoHS directive (2002/95/EC).
Object substances: lead, mercury, cadmium, hexavalent chromium, polybrominated biphenyls (PBB) and polybrominated diphenyl ethers (PBDE)

• Content of six substances specified in " Management Methods for Control of Pollution Caused by Electronic Information Products Regulation " (Chinese : 电子信息产品污染控制管理办法)

Category	Toxic and hazardous substances					
	Lead (Pb)	Mercury (Hg)	Cadmium (Cd)	Hexavalent chromium (Cr^{6+})	Polybrominated biphenyls (PBB)	Polybrominated diphenyl ethers (PBDE)
Infrared data communication device	✓	✓	✓	✓	✓	✓

✓: indicates that the content of the toxic and hazardous substance in all the homogeneous materials of the part is below the concentration limit requirement as described in SJ/T 11363-2006 standard.

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--- Office automation equipment
--- Telecommunication equipment [terminal]
--- Test and measurement equipment
--- Industrial control
--- Audio visual equipment
--- Consumer electronics
(ii) Measures such as fail-safe function and redundant design should be taken to ensure reliability and safety when SHARP devices are used for or in connection with equipment that requires higher reliability such as:
--- Transportation control and safety equipment (i.e., aircraft, trains, automobiles, etc.)
--- Traffic signals
--- Gas leakage sensor breakers
--- Alarm equipment
--- Various safety devices, etc.
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--- Telecommunication equipment [trunk lines]
--- Nuclear power control equipment
--- Medical and other life support equipment (e.g., scuba).

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